

100V N-Channel MOSFETs

General Description

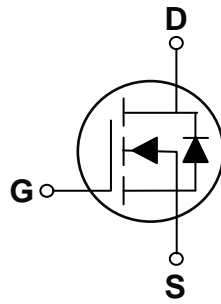
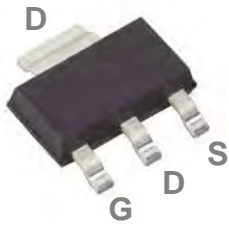
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
100V	310mΩ	1.7A

Features

- 100V, 1.7A , $R_{DS(ON)}=310m\Omega @V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

SOT223 Pin Configuration



Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings $T_c=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_c=25^\circ\text{C}$)	1.7	A
	Drain Current – Continuous ($T_c=100^\circ\text{C}$)	1.08	A
I_{DM}	Drain Current – Pulsed ¹	6.8	A
P_D	Power Dissipation ($T_c=25^\circ\text{C}$)	1.76	W
	Power Dissipation – Derate above 25°C	0.014	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-50 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	70	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	30	$^\circ\text{C}/\text{W}$



FTK0954T

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Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to $25\text{ }^\circ\text{C}$, $I_D=1mA$	---	0.09	---	V/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V, V_{GS}=0V, T_J=25\text{ }^\circ\text{C}$	---	---	1	μA
		$V_{DS}=80V, V_{GS}=0V, T_J=125\text{ }^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=1A$	---	260	310	m Ω
		$V_{GS}=4.5V, I_D=0.5A$	---	270	320	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.8	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5	---	mV/ $^\circ\text{C}$
g_{fs}	Forward Transconductance	$V_{DS}=10V, I_D=2A$	---	2.3	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$V_{DS}=50V, V_{GS}=10V, I_D=1A$	---	9	18	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	2.3	4.6	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	1.1	2.5	
$T_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DD}=50V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=1A$	---	5.2	10	ns
T_r	Rise Time ^{2,3}		---	6.8	12	
$T_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	14.5	28	
T_f	Fall Time ^{2,3}		---	2.1	5	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, F=1MHz$	---	492	800	pF
C_{oss}	Output Capacitance		---	27	50	
C_{rss}	Reverse Transfer Capacitance		---	15	25	
R_g	Gate resistance		$V_{GS}=0V, V_{DS}=0V, F=1MHz$	---	2.8	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	4	A
I_{SM}	Pulsed Source Current		---	---	8	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=1A, T_J=25\text{ }^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time ²	$I_S=1A, di/dt=100A/\mu s$	---	---	---	ns
Q_{rr}	Reverse Recovery Charge ²	$T_J=25\text{ }^\circ\text{C}$	---	---	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

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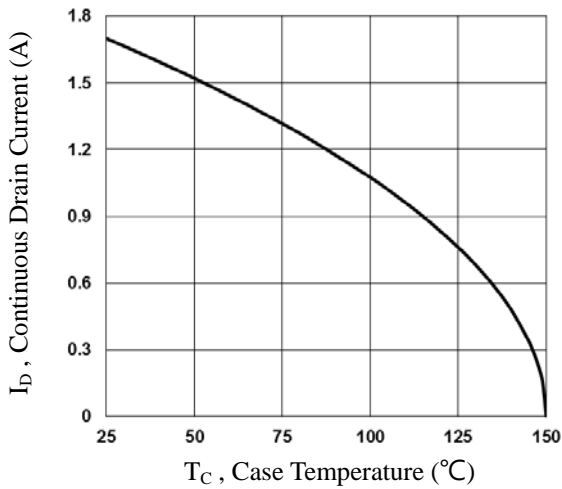


Fig.1 Continuous Drain Current vs. T_C

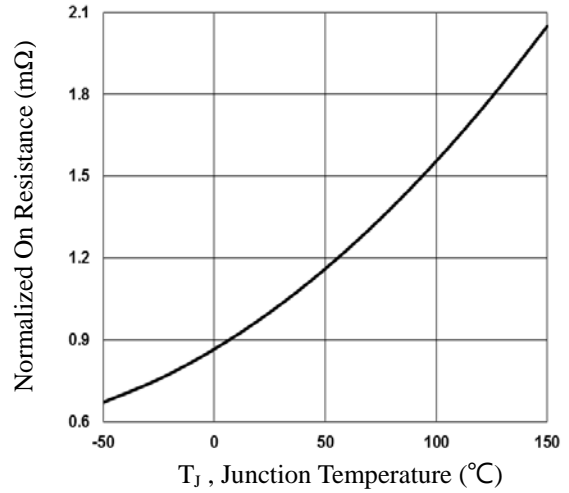


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

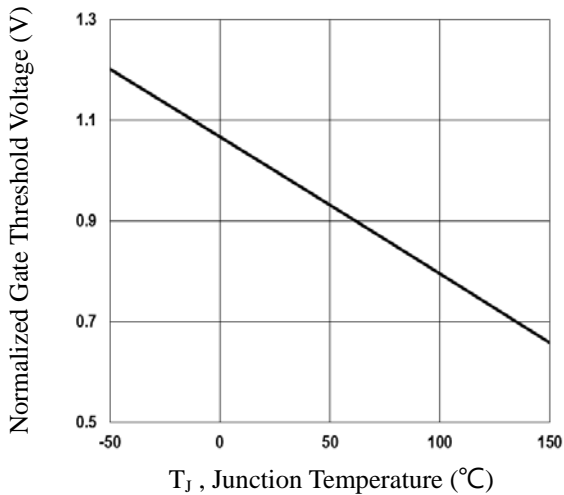


Fig.3 Normalized V_{th} vs. T_J

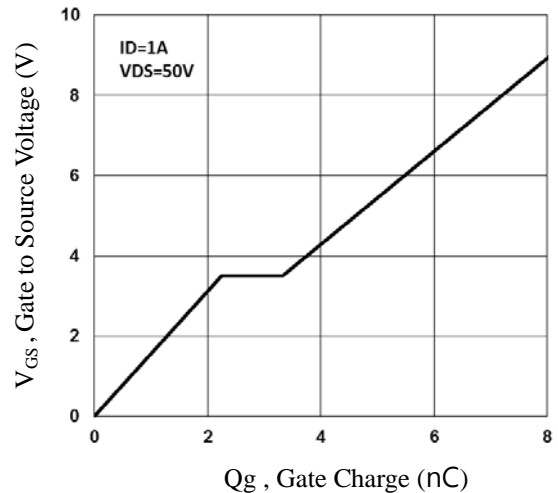


Fig.4 Gate Charge Waveform

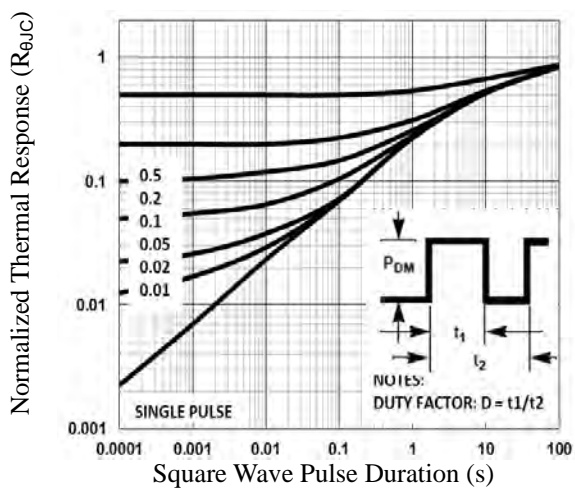


Fig.5 Normalized Transient Impedance

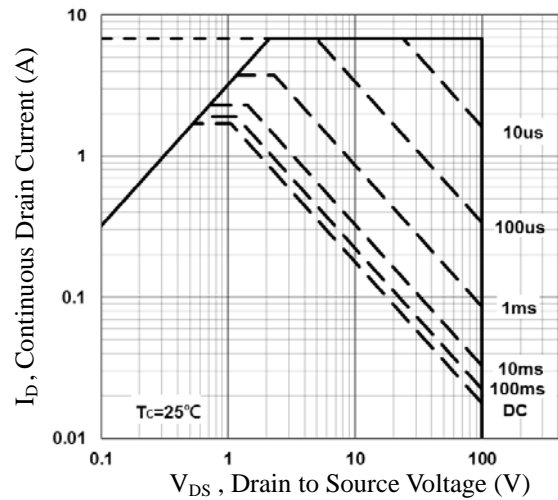


Fig.6 Maximum Safe Operation Area

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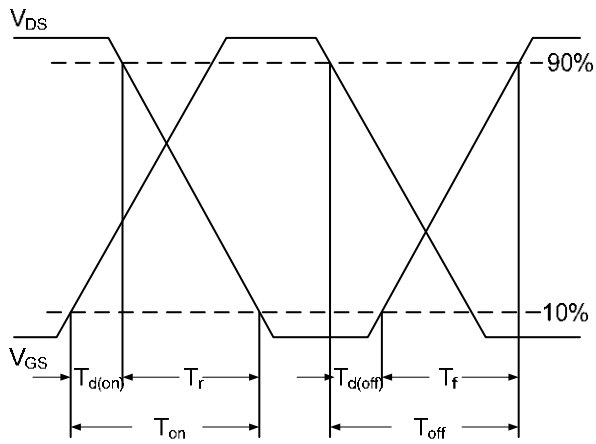


Fig.7 Switching Time Waveform

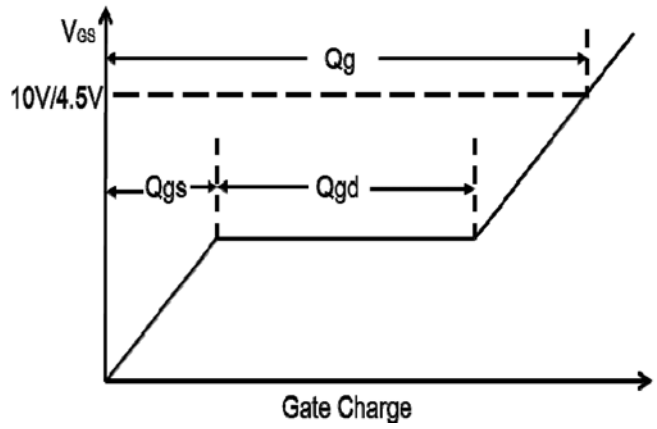
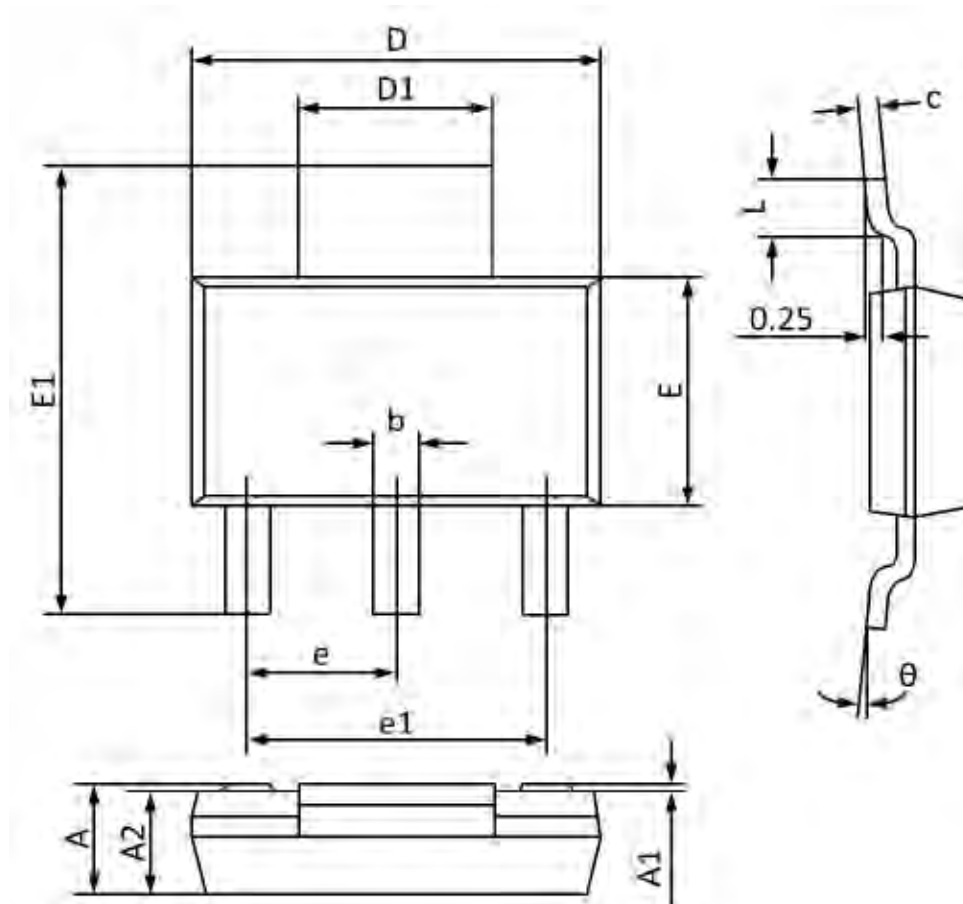


Fig.8 Gate Charge Waveform

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SOT223 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.520	1.800	0.060	0.071
A1	0.000	0.100	0.000	0.004
A2	1.500	1.700	0.059	0.067
b	0.660	0.820	0.026	0.032
c	0.250	0.350	0.010	0.014
D	6.200	6.400	0.244	0.252
D1	2.900	3.100	0.114	0.122
E	3.300	3.700	0.130	0.146
E1	6.830	7.070	0.269	0.278
e	2.300 (BSC)		0.091 (BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.150	0.035	0.045
θ	0°	10°	0°	10°